



Sandisk Announces Sampling of BiCS10 1Tb TLC 3D NAND Flash Memory Pushing Density, Power Efficiency and Performance to Support Data-Intensive Workloads

July 2, 2026

*BiCS10 TLC delivers up to 4.8Gb/s** NAND interface speed, 59 percent bit density improvement compared to BiCS8 and enhanced power efficiency*

MILPITAS, Calif.--(BUSINESS WIRE)--Jul. 2, 2026-- Sandisk Corporation (Nasdaq: SNDK) today announced it is sampling its BiCS10 1Tb TLC, its 10th-generation 3D NAND flash memory technology. BiCS10 applies advanced lateral scaling techniques to achieve industry-leading 1Tb TLC memory density greater than 29Gb/mm², improving bit density by 59 percent while delivering up to 4.8Gb/s** interface speed, a 33 percent improvement compared with 8th generation 3D flash memory currently in mass production.

Built on Sandisk's proven Bit-Cost Scalable (BiCS) 3D NAND architecture and CMOS directly Bonded to Array (CBA) technology, BiCS10 TLC also enhances data input/output power efficiency, reducing power consumption by 10 percent for input and 34 percent for output compared to the previous BiCS8 generation.

"As the world becomes more connected, data-intensive and intelligent, NAND plays an increasingly mission-critical role in delivering the performance, efficiency and scale modern computing requires," said Alper Ilkbahar, CTO at Sandisk. "BiCS8 set a new benchmark for 3D NAND by combining our wafer bonding capabilities with meaningful gains in density, performance, and efficiency. With BiCS10 TLC, we build upon that proven foundation to deliver faster interface speeds, higher bit density and improved power efficiency for our customers."

NAND flash memory is one of the most scalable semiconductor technologies today, and the foundation of what Sandisk builds. BiCS10 advances Sandisk's long-term roadmap for scaling NAND through continued innovation in density, power efficiency, and architecture. It builds upon Sandisk's CBA technology, which fabricates CMOS logic and the memory array on separate wafers before bonding them together with high-precision wafer-to-wafer alignment. BiCS10 TLC increases the number of memory layers to 332 and incorporates Toggle DDR6.0, SCA protocol and PI-LTT technology to support high-speed, low-power operation.

The sampling milestone extends Sandisk's BiCS roadmap with advancements that push density, power efficiency, and endurance in ways designed to support the next generation of data-intensive and AI-driven workloads. Key BiCS10 TLC technology highlights include:

- Up to 4.8Gb/s** NAND interface speed, a 33 percent improvement.*
- 332 memory layers with optimized floor plan efficiency, improving bit density by 59 percent.*
- Enhanced data input/output power efficiency, reducing power consumption by 10 percent for input and 34 percent for output.*
- Support for Toggle DDR6.0, SCA protocol¹ and PI-LTT technology² to enable high-speed, low-power operation.

Sandisk leads the way in flash innovation, from increasing bits per cell over time to advancing technologies in controller architecture, firmware, packaging, and system flash that improve the performance, efficiency, and utility of flash at scale. With a unique portfolio of leading IP and global manufacturing footprint, Sandisk controls its entire production lifecycle from design to manufacturing to final assembly with global operations, resulting in exceptional quality control, cost efficiency, faster time to market, and strong supply chain resilience.

About Sandisk

Sandisk (Nasdaq: SNDK) delivers innovative Flash solutions and advanced memory technologies that meet people and businesses at the intersection of their aspirations and the moment, enabling them to keep moving and pushing possibility forward. Follow Sandisk on [Instagram](#), [Facebook](#), [X](#), [LinkedIn](#), [YouTube](#). Join [TeamSandisk](#) on Instagram.

*Compared with 8th-generation 3D flash memory currently in mass production (BiCS8).

** 1Gb/s is calculated as 1,000,000,000 bits/second. This value is obtained under specific our test environment and may vary depending on use conditions.

¹ Technology wherein the bus for Command/Address input and the bus for data transfer are completely separated into different buses and are used in parallel. This reduces data input/output time.

² Technology wherein power sources for existing 1.2V and additional lower voltage are utilized for the NAND interface power source. This reduces power consumption during data input/output.

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Forward-Looking Statements

This press release contains forward-looking statements within the meaning of U.S. federal securities laws, including, without limitation, statements regarding the expected performance, enhanced capabilities, and industry-leading positioning of Sandisk's BiCS10 TLC technology; the role of NAND flash memory as a highly scalable, mission-critical technology for modern computing; Sandisk's continued advancement of its long-term roadmap; and the impact, advancements and efficiency of Sandisk's flash solutions in supporting next-generation data-intensive and AI-driven workloads. These forward-looking statements are based on current expectations and are subject to risks and uncertainties that could cause actual results to differ materially from those expressed or implied in the forward-looking statements.

Key risks and uncertainties that could cause actual results to differ materially from those expressed or implied in the forward-looking statements include: adverse changes in global or regional economic conditions, including the impact of evolving trade policies, tariff regimes and trade wars; volatility in demand for Sandisk's products; pricing trends and fluctuations in average selling prices; exposure to execution, financial and market risks due to long-term agreements; inflation; changes in interest rates and a potential economic recession; the impact of business and market conditions; the impact of competitive products and pricing; the development and introduction of products based on new technologies and management of technology transitions; risks associated with strategic initiatives, including restructurings, acquisitions, divestitures, cost saving measures and joint ventures; risks related to product defects; difficulties or delays in manufacturing or other supply chain disruptions; reliance on strategic relationships with key partners, including Kioxia Corporation; the attraction, retention and development of skilled management and technical talent; risks associated with the use of artificial intelligence in business operations; changes to relationships with key customers or consolidation among the customer base; compromise, damage or interruption from cybersecurity incidents or other data system security risks; reliance on intellectual property; fluctuations in currency exchange rates; actions by competitors; risks associated with compliance with changing legal and regulatory requirements; and other risks and uncertainties listed in Sandisk's filings with the Securities and Exchange Commission, including its Annual Report on Form 10-K filed with the SEC on August 21, 2025 and Quarterly Report on Form 10-Q filed with the SEC on May 1, 2026, to which your attention is directed. You should not place undue reliance on these forward-looking statements, which speak only as of the date hereof, and Sandisk undertakes no obligation to update or revise these forward-looking statements to reflect new information or events, except as required by law.

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Source: Sandisk Corporation